

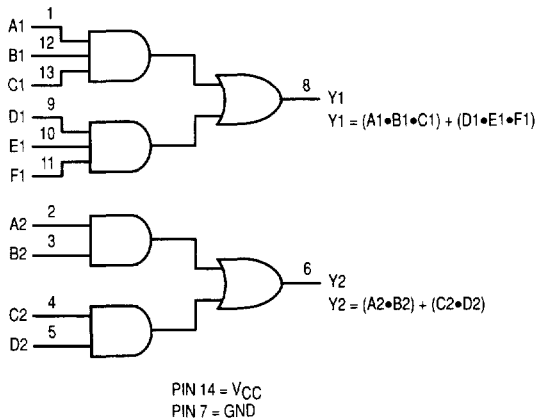
2-Wide, 2-Input/2-Wide, 3-Input AND-OR Gates

High-Performance Silicon-Gate CMOS

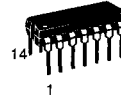
The MC74HC58 is identical to the MC74HC51 except that the outputs are inverted. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 42 FETs or 10.5 Equivalent Gates

LOGIC DIAGRAM



MC74HC58



N SUFFIX
PLASTIC PACKAGE
CASE 646-06

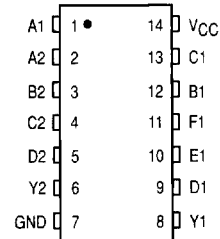


D SUFFIX
SOIC PACKAGE
CASE 751A-03

ORDERING INFORMATION

MC74HCXXN Plastic
MC74HCXXD SOIC

PIN ASSIGNMENT



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FUNCTION TABLES

Inputs						Output
A1	B1	C1	D1	E1	F1	Y1
H	H	H	X	X	X	H
X	X	X	H	H	H	H
Any other combinations						L

Inputs				Output
A2	B2	C2	D2	Y2
H	H	X	X	H
X	X	H	H	H
Any other combinations				L



MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 1.5 to V _{CC} + 1.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

* Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

† Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C
SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V	
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C	
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

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DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit				
				- 55 to 25°C	≤ 85°C	≤ 125°C					
V _{IH}	Minimum High-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	1.5	1.5	1.5	V				
			4.5	3.15	3.15	3.15					
			6.0	4.2	4.2	4.2					
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	0.3	0.3	0.3	V				
			4.5	0.9	0.9	0.9					
			6.0	1.2	1.2	1.2					
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0	1.9	1.9	1.9	V				
			4.5	4.4	4.4	4.4					
			6.0	5.9	5.9	5.9					
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0	0.1	0.1	0.1	V				
			4.5	0.1	0.1	0.1					
			6.0	0.1	0.1	0.1					
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA				
			I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0		2	20	40	μA
			I _{out}								

NOTE: Information on typical parametric values can be found in Chapter 2.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			- 55 to 25°C	$\leq 85^\circ\text{C}$	$\leq 125^\circ\text{C}$	
PLH, tPHL	Maximum Propagation Delay, Any Input to Output Y (Figures 1 and 2)	2.0	125	155	190	ns
		4.5	25	31	38	
		6.0	21	26	32	
tTLH, tTHL	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0	75	95	110	ns
		4.5	15	19	22	
		6.0	13	16	19	
C_{in}	Maximum Input Capacitance	—	10	10	10	pF

NOTES:

1. For propagation delays with loads other than 50 pF, see Chapter 2.
2. Information on typical parametric values can be found in Chapter 2.

C_{pD}	Power Dissipation Capacitance (Per Section)*	Typical @ 25°C, $V_{CC} = 5.0 \text{ V}$	Unit
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* Used to determine the no-load dynamic power consumption: $P_D = C_{pD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2.

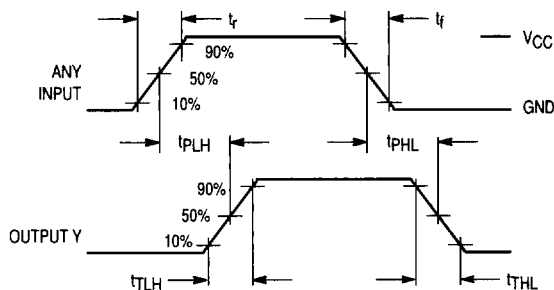
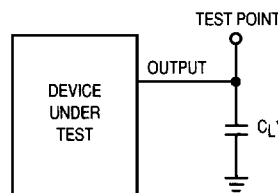


Figure 1. Switching Waveforms

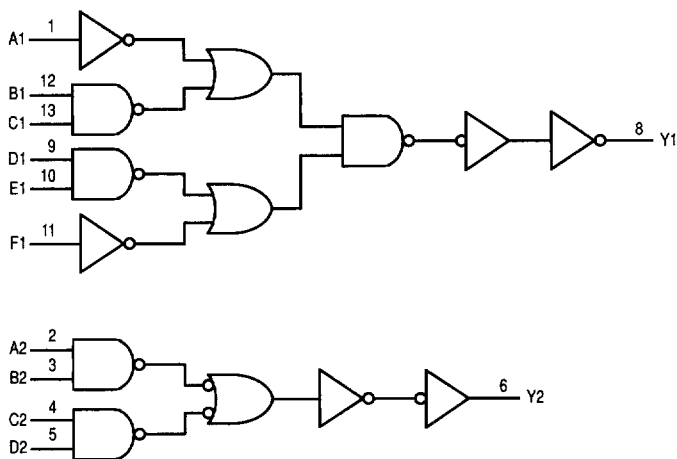


* Includes all probe and jig capacitance

Figure 2. Test Circuit

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EXPANDED LOGIC DIAGRAM



PIN 14 = V_{CC}
PIN 7 = GND